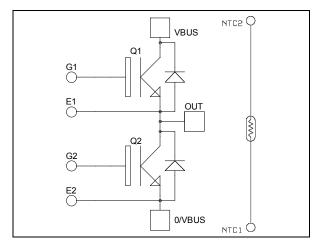
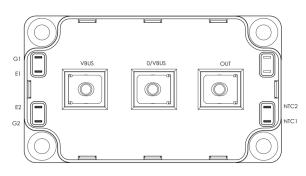


Phase leg High speed Trench + Field Stop IGBT4 Power module







Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- High speed Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
- Kelvin source for easy drive
- Very low stray inductance
- M5 power connectors
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

All ratings @ $T_j = 25$ °C unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Voltage		650	V
Ţ	Continuous Callacter Current	$T_C = 25^{\circ}C$	770*	
I_{C}	Continuous Collector Current	$T_C = 60^{\circ}C$	600*	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	1500	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25^{\circ}C$	2000	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	1200A @ 600V	

^{*} Specification of device but current must be limited due to size of power connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				600	μA
V _{CE(sat)}	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.85	2.3	V
		$I_C = 600A$ $T_j = 150$	$T_j = 150$ °C		2.2		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 3.2 \text{ mA}$		4.2	5.1	5.6	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				1	μA

Dynamic Characteristics (per IGBT)

·	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			36.6		
C_{oes}	Output Capacitance				1.3		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz			1.08		
Q_{G}	Gate charge	$V_{GE} = 15V$; $V_{CE} = 480V$ $I_{C} = 600A$			3500		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ning (25°C)		19		ns
T_{r}	Rise Time	$V_{GE} = \pm 15V$			33		
$T_{d(off)}$	Turn-off Delay Time	$V_{CE} = 400V$ $I_{C} = 600A$			197		
$T_{\rm f}$	Fall Time	$R_G = 0.6\Omega$		21			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 400V$ $I_{C} = 600A$ $R_{G} = 0.6\Omega$			19		ns
$T_{\rm r}$	Rise Time				29		
$T_{d(off)}$	Turn-off Delay Time				227		
T_{f}	Fall Time				22		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25^{\circ}C$		12		mJ
011	2 23	$V_{CE} = 400V$	$T_{\rm J} = 150^{\circ}{\rm C}$		14.7		
E_{off}	Turn-off Switching Energy	$I_{\rm C} = 600 A$ $R_{\rm G} = 0.6 \Omega$	$T_{J} = 25^{\circ}C$ $T_{J} = 150^{\circ}C$		11.2		mJ
I_{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 600V$ $t_p \le 10 \mu s$; $T_j = 150 ^{\circ}C$			3900		A
R_{thJC}	Junction to Case Thermal Resistance					0.075	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Repetitive Reverse Voltage					650	V
I_{RM}	Reverse Leakage Current	$V_R = 650V$				300	μΑ
I_F	DC Forward Current		$T_c = 25^{\circ}C$		600		A
V	Diode Forward Voltage	$I_F = 600A$ $V_{GE} = 0V$	$T_j = 25$ °C		1.6	2	V
V_{F}			$T_{j} = 150^{\circ}C$		1.5		
_	D D Tim-	verse Recovery Time $I_F = 600A$ $V_R = 400V$ $di/dt = 7000A/\mu s$	$T_j = 25$ °C		125		
t_{rr}	Reverse Recovery Time		$T_{\rm j} = 150^{\circ}{\rm C}$		220		ns
0	Payarga Pagayary Charga		$T_j = 25$ °C		28.1		μC
Q _{rr}	di/dt = 7000 A/ μ s $T_j = 150$ °C				59.3		μС
E_{r}	Reverse Recovery Energy	·	$T_j = 25^{\circ}C$		6.6		mJ
⊥ r	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		14.4		1113
R_{thJC}	Junction to Case Thermal Resistance					0.13	°C/W



$Temperature\ sensor\ NTC\ (\text{see application note APT0406 on www.microsemi.com}).$

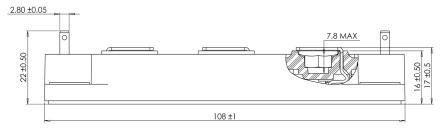
Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C	stance @ 25°C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		$T_C=100$ °C		4		%

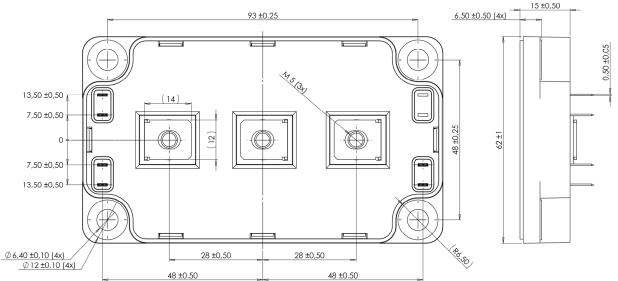
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature} \quad R_T: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000		V
T_{J}	Operating junction temperature range			-40	175	
T_{JOP}	Recommended junction temperature under switching conditions Storage Temperature Range				T _J max -25	°C
T_{STG}					125	C
$T_{\rm C}$	Operating Case Temperature				100	
Torque	Mounting torque	To Heatsink	M6	3	5	N.m
Torque	Mounting torque	For teminals	M5	2	3.5	IN.III
Wt	Package Weight				300	g

SP6 Package outline (dimensions in mm)

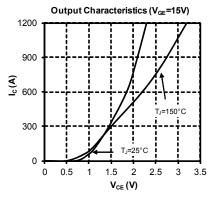


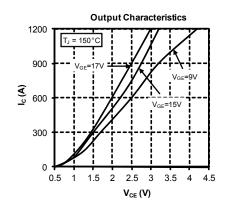


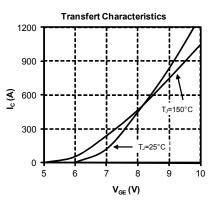
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

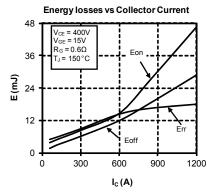


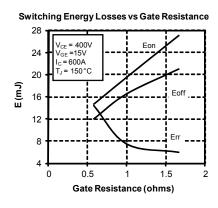
Typical Performance Curve

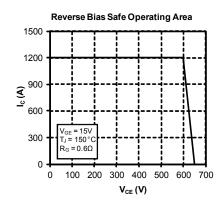


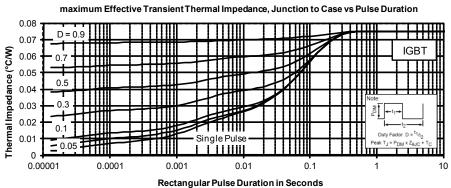




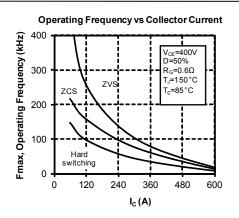


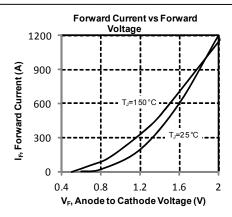




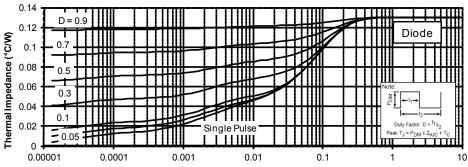












Rectangular Pulse Duration in Seconds



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